

FIG. 1A

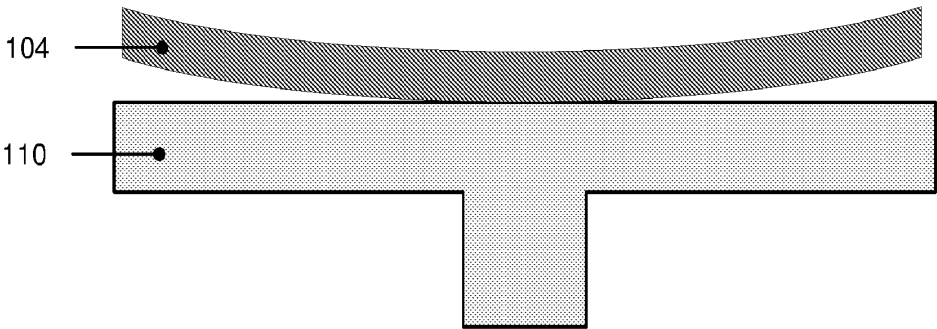
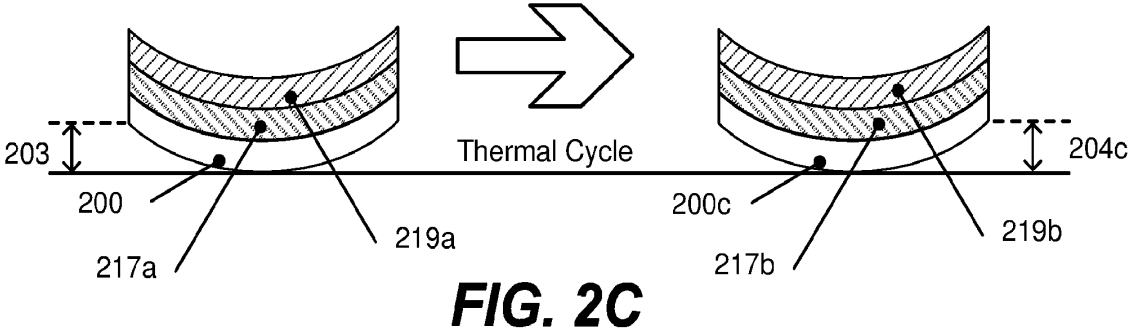
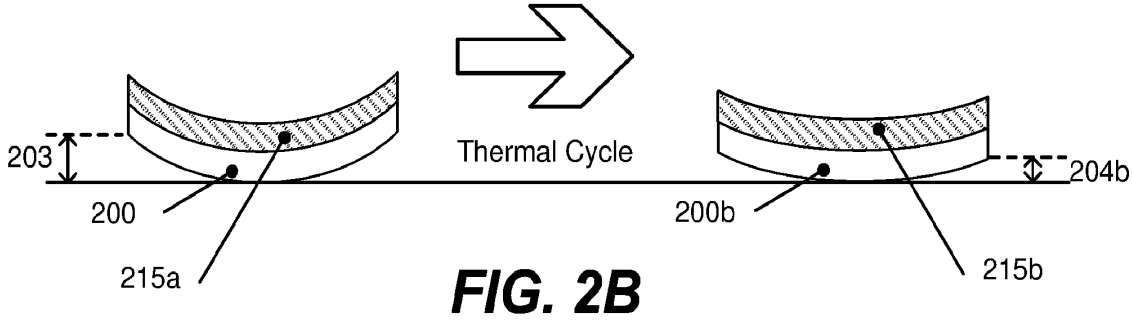
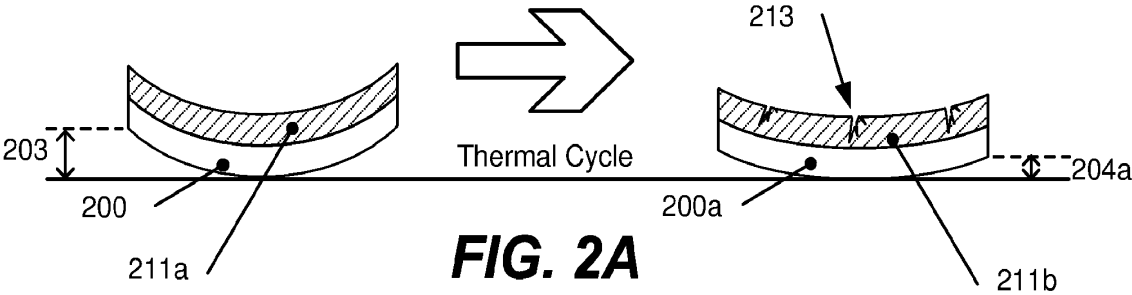


FIG. 1B



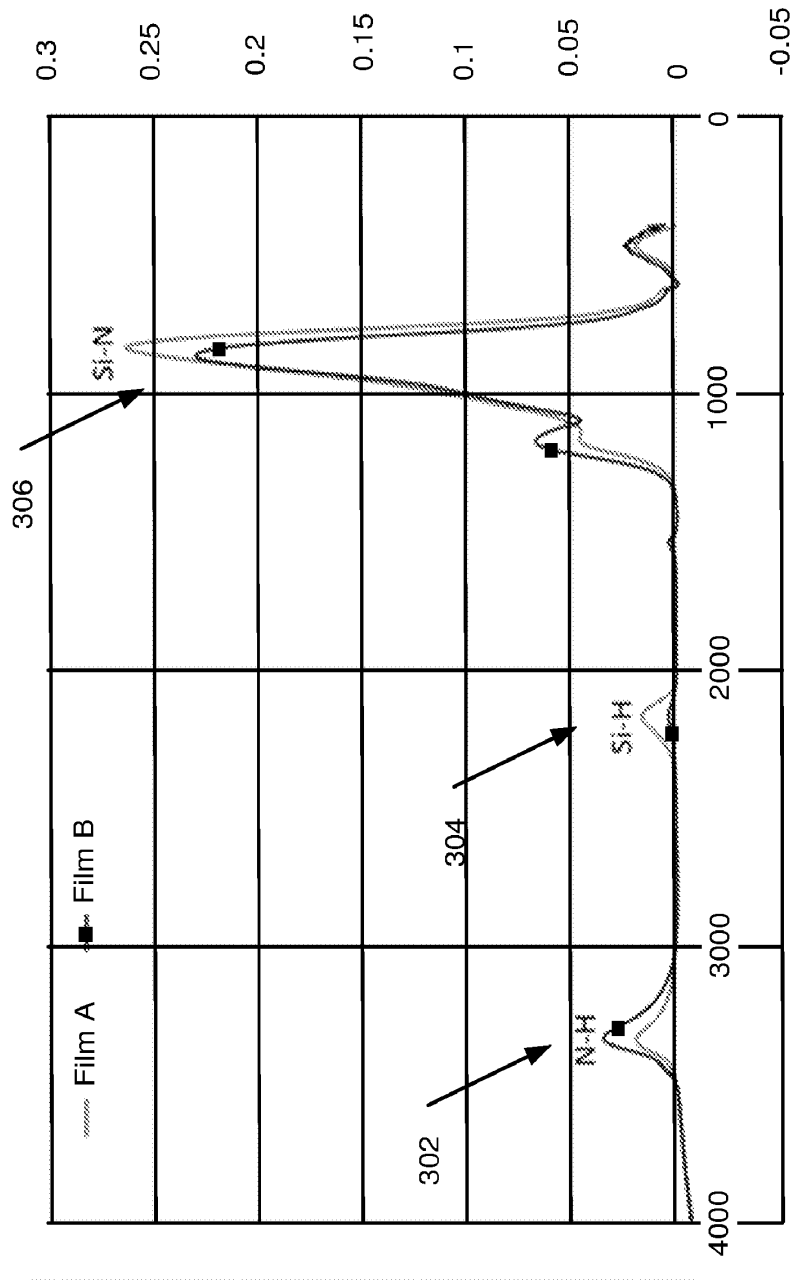
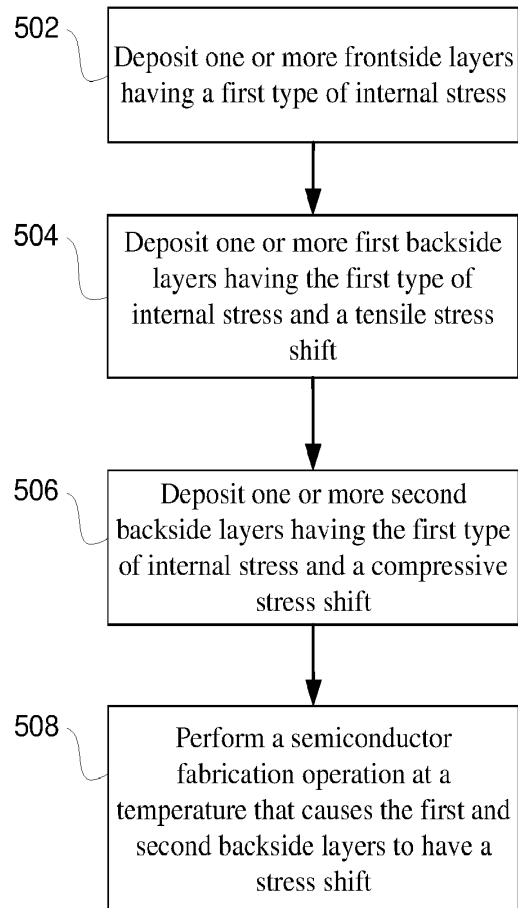


FIG. 3

Film	As-Deposited (350°C) film stress (MPa)	Post anneal (850°C) Film Stress (MPa)	%Stress Shift Post- Anneal	Maximum Wafer Bow Post-850°C Anneal Without Film Cracking
SiN Film A	550	920	68%	170μm
SiN Film B	470	226	-52%	150μm
SiN Film A+B	500	497	-0.60%	270μm

FIG. 4

**FIG. 5**

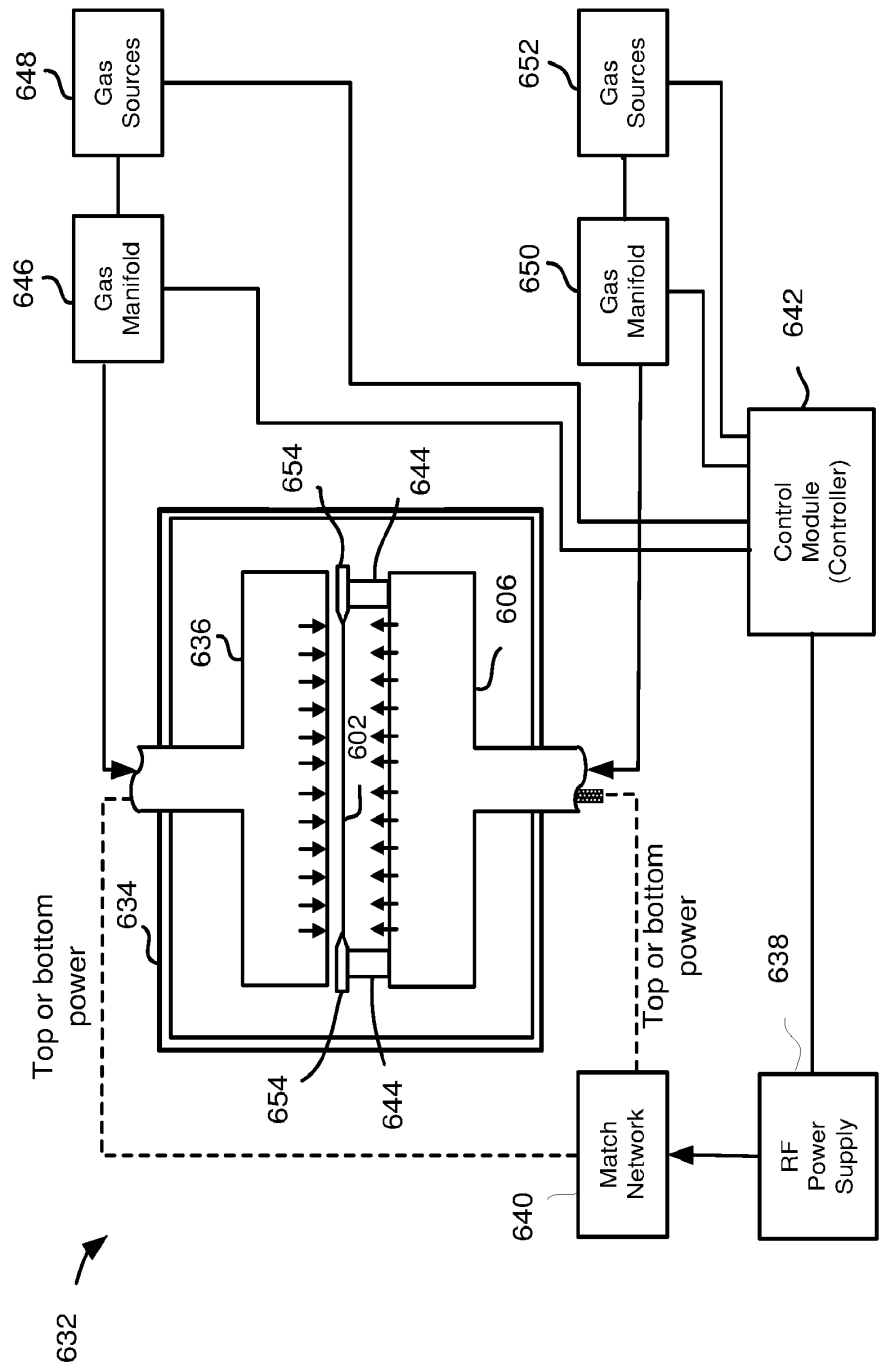


FIG. 6A

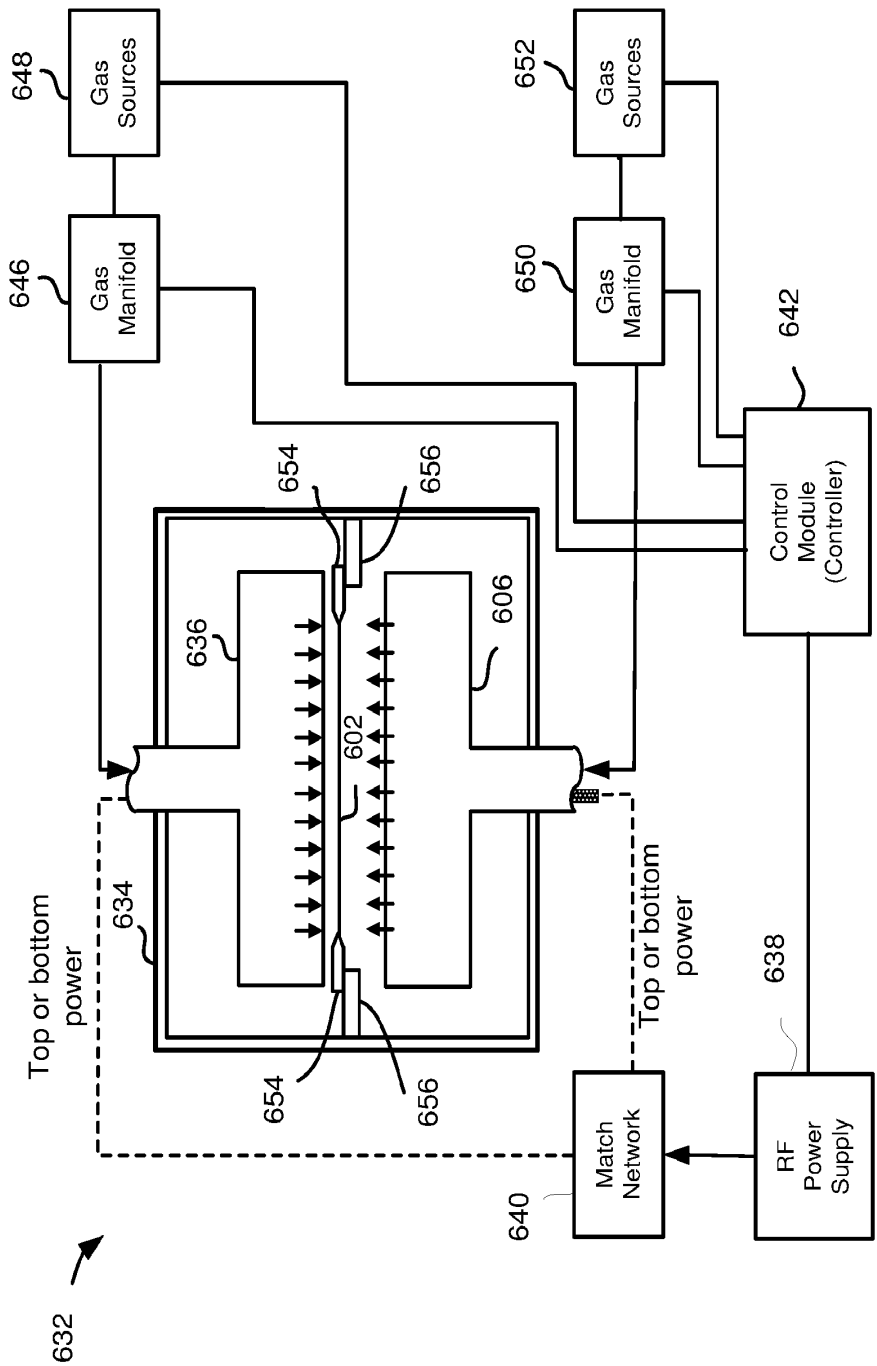


FIG. 6B

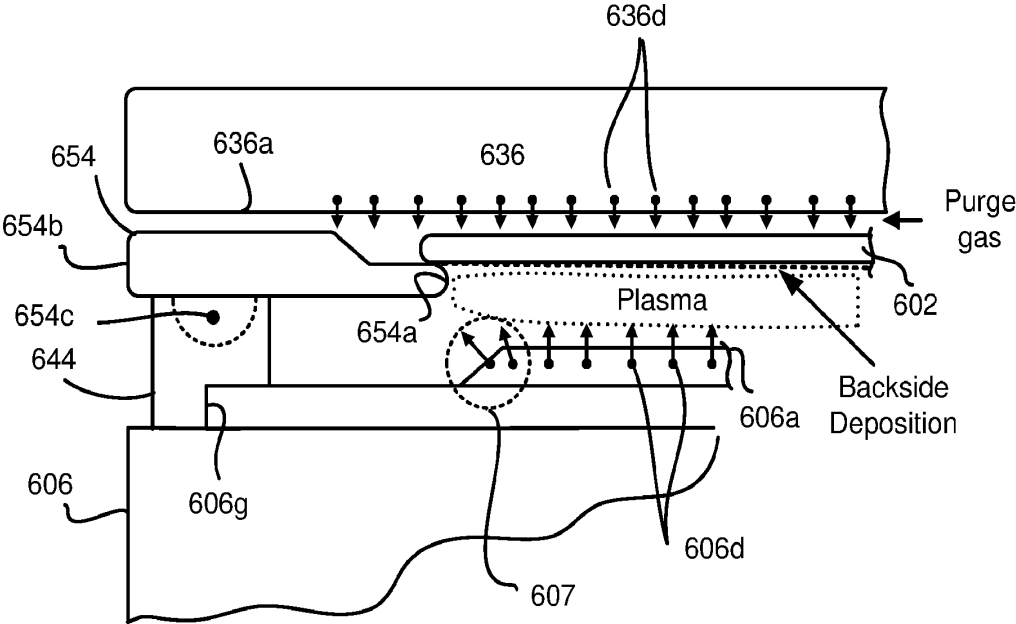


FIG. 7A

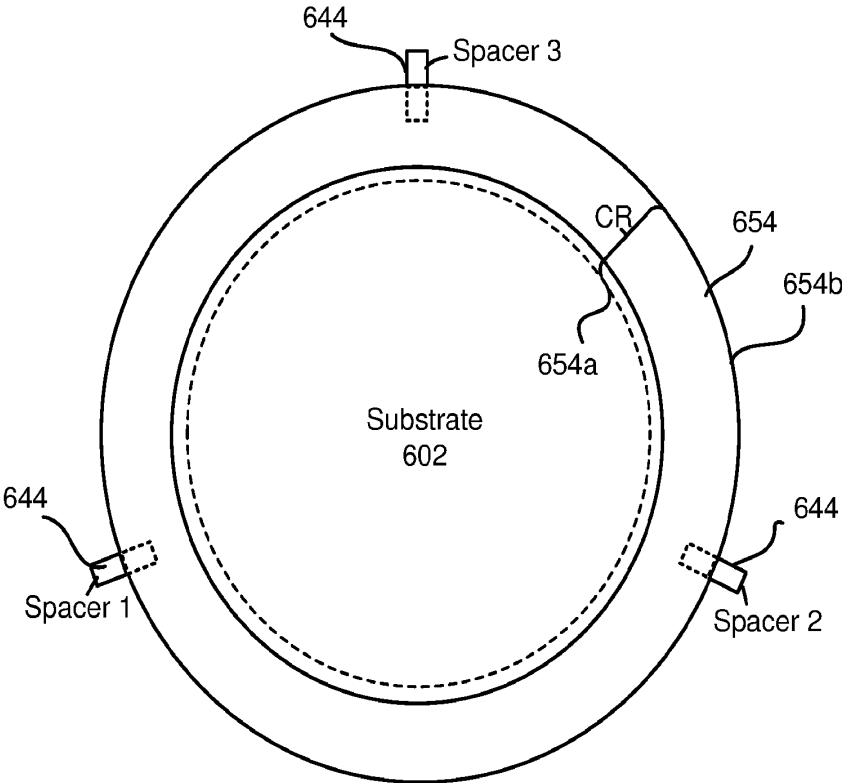


FIG. 7B

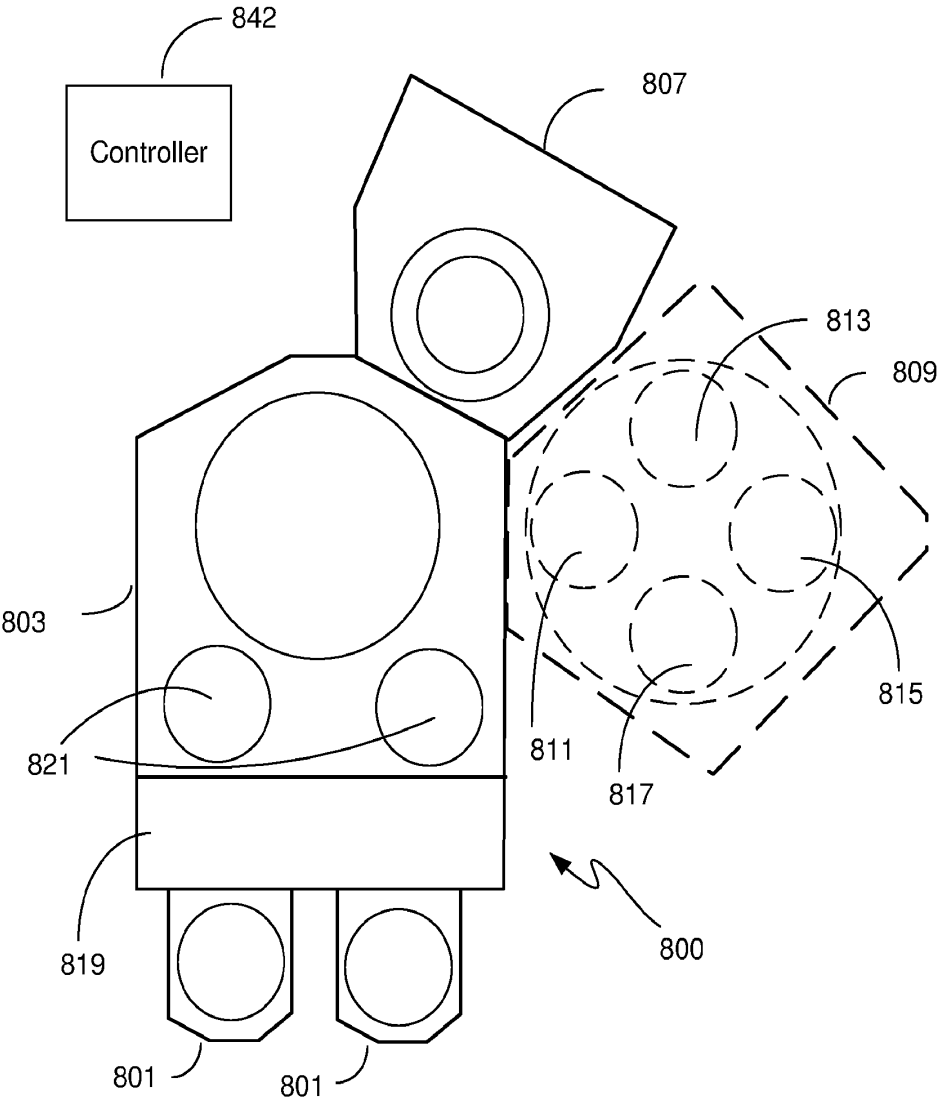


FIG. 8